

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Applicant proposes amending claims 80, 81, 88, 89, 97, 98, 100, 101, 106, 107, 109, and 110 as follows:

Listing of Claims:

1-79. (Cancelled)

80. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer in situ to a reducing environment;

depositing a second conductive layer; and

exposing the ~~wafer~~ second conductive layer to a material selected from the group consisting of diborane and HCl, wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

81. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer onto the wafer;

exposing the wafer in situ to a reducing environment;

depositing a second conductive layer; and

exposing the ~~wafer~~ first conductive layer to a material selected from the group consisting of diborane and HCl, wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

82. (Previously Presented) The method of claim 80 further comprising forming a third conductive layer on the second conductive layer.

83. (Previously Presented) The method of claim 82 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

84. (Previously Presented) The method of claim 83 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

85-87. (Cancelled)

88. (Currently Amended) A method of treating a wafer, comprising:  
depositing a first conductive layer onto the wafer;  
exposing the wafer to a reducing environment;  
depositing a second conductive layer; and  
passivating ~~at least one of the first and second conductive layers~~  
the second conductive layer by exposing the ~~wafer~~ second conductive layer to a material selected from the group consisting of diborane and HCl, wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

89. (Currently Amended) A method of treating a wafer, comprising:  
depositing a first conductive layer onto the wafer;  
exposing the wafer to a reducing environment;  
depositing a second conductive layer; and  
passivating ~~at least one of the first and second conductive layers~~  
the first conductive layer by exposing the ~~wafer~~ first conductive layer to a material selected from the group consisting of diborane and HCl, wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

90. (Previously Presented) The method of claim 88 further comprising forming a third conductive layer on the second conductive layer.

91. (Previously Presented) The method of claim 90 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

92. (Previously Presented) The method of claim 91 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

93. (Previously Presented) The method of claim 81 further comprising forming a third conductive layer on the second conductive layer.

94. (Previously Presented) The method of claim 93 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

95. (Previously Presented) The method of claim 94 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

96. (Previously Presented) The method of claim 81 wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas.

97. (Currently Amended) The method of claim 81 wherein exposing the ~~wafer~~ first conductive layer to a material selected from the group consisting of diborane and HCl comprises exposing the ~~wafer~~ first conductive layer to this selection prior to exposing the wafer in situ to a reducing environment.

98. (Currently Amended) The method of claim 81 wherein exposing the ~~wafer~~ first conductive layer to a material selected from the group consisting of diborane and HCl comprises exposing the ~~wafer~~ first conductive layer to this selection prior to depositing the second conductive layer.

99. (Previously Presented) The method of claim 80 wherein exposing the wafer in situ to a reducing environment comprises exposing the wafer to silane gas.

100. (Currently Amended) The method of claim 80 wherein exposing the ~~wafer~~ second conductive layer to a material selected from the group consisting of diborane and HCl comprises exposing the ~~wafer~~ second conductive layer to this selection prior to exposing the wafer in situ to a reducing environment.

101. (Currently Amended) The method of claim 80 wherein exposing the ~~wafer~~ second conductive layer to a material selected from the group consisting of diborane and HCl comprises exposing the ~~wafer~~ second conductive layer to this selection prior to depositing the second conductive layer.

102. (Previously Presented) The method of claim 89 further comprising forming a third conductive layer on the second conductive layer.

103. (Previously Presented) The method of claim 102 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

104. (Previously Presented) The method of claim 103 wherein the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and the third conductive layer comprises polysilicon.

105. (Previously Presented) The method of claim 89 wherein exposing the wafer to a reducing environment comprises exposing the wafer to silane gas.

106. (Currently Amended) The method of claim 89 wherein exposing the ~~wafer~~ first conductive layer to a material selected from the group consisting of diborane, phosphine, and HCL, ~~and boron trichloride~~ comprises exposing the ~~wafer~~ first conductive layer to this selection prior to exposing the wafer to a reducing environment.

107. (Currently Amended) The method of claim 89 wherein exposing the ~~wafer~~ first conductive layer to a material selected from the group consisting of diborane,